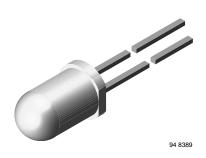
HALOGEN



## Vishay Semiconductors

## High Power Infrared Emitting Diode, 940 nm, GaAlAs/GaAs



## **DESCRIPTION**

TSAL6200 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power molded in a blue-gray plastic package.

## **FEATURES**

Package type: leaded
Package form: T-1¾
Dimensions (in mm): Ø 5

• Peak wavelength:  $\lambda_p = 940 \text{ nm}$ 

High reliability

High radiant power

· High radiant intensity

• Angle of half intensity:  $\phi = \pm 17^{\circ}$ 

· Low forward voltage

- Suitable for high pulse current operation
- · Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

## **APPLICATIONS**

- · Infrared remote control units with high power requirements
- Free air transmission systems
- · Infrared source for optical counters and card readers

PRODUCT SUMMARY					
COMPONENT	l <sub>e</sub> (mW/sr)	φ (deg)	λ <sub>P</sub> (nm)	t <sub>r</sub> (ns)	
TSAL6200	60	± 17	940	800	

### Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSAL6200	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾		

### Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	5	V	
Forward current		I <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1.5	Α	
Power dissipation		P <sub>V</sub>	160	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T <sub>amb</sub>	- 40 to + 85	°C	
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R <sub>thJA</sub>	230	K/W	

#### Note

T<sub>amb</sub> = 25 °C, unless otherwise specified

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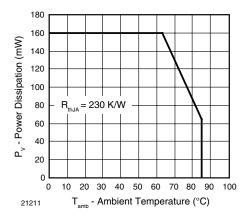


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

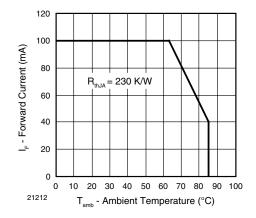


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>		1.35	1.6	V
	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	V <sub>F</sub>		2.6	3	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>VF</sub>		- 1.8		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			10	μΑ
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	C <sub>j</sub>		25		pF
De die at het en etc.	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l <sub>e</sub>	40	60	200	mW/sr
Radiant intensity	$I_F = 1 \text{ A}, t_p = 100 \ \mu\text{s}$	l <sub>e</sub>	340	500		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	φe		35		mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 20 mA	TKφe		- 0.6		%/K
Angle of half intensity		φ		± 17		deg
Peak wavelength	I <sub>F</sub> = 100 mA	$\lambda_{p}$		940		nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		50		nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>		0.2		nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>		800		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		800		ns
Virtual source diameter	Method: 63 % encircled energy	d		2.4		mm

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified



## High Power Infrared Emitting Diode, Vishay Semiconductors 940 nm, GaAlAs/GaAs

## **BASIC CHARACTERISTICS**

 $T_{amb}$  = 25 °C, unless otherwise specified

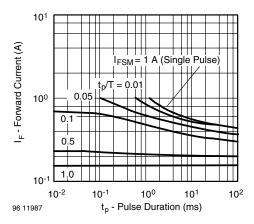


Fig. 3 - Pulse Forward Current vs. Pulse Duration

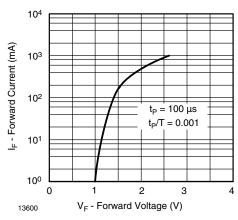


Fig. 4 - Forward Current vs. Forward Voltage

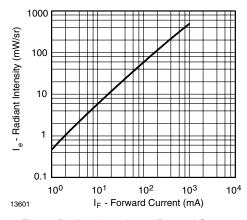


Fig. 5 - Radiant Intensity vs. Forward Current

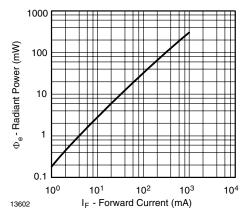


Fig. 6 - Radiant Power vs. Forward Current

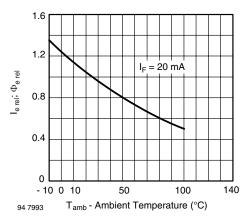


Fig. 7 - Relative Radiant Intensity/Power vs. Ambient Temperature

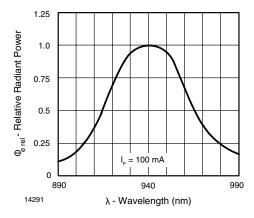


Fig. 8 - Relative Radiant Power vs. Wavelength

# Vishay Semiconductors High Power Infrared Emitting Diode, 940 nm, GaAlAs/GaAs



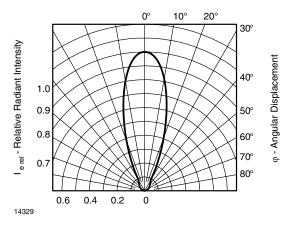
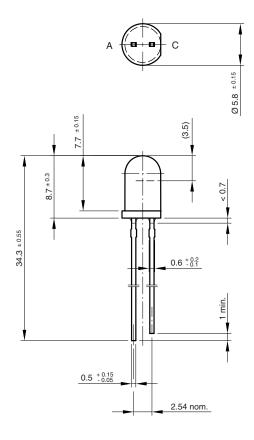
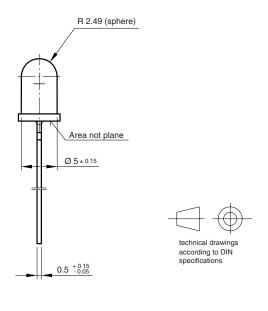


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

## **PACKAGE DIMENSIONS** in millimeters





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19257





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